JIEJIE MICROELECTRONICS CO., LTD.

T0820H-8K 8A TRIAC

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Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	40	mA
				55	
I_H	I_T =100mA		MAX.	30	mA
dV/dt	V_D=540V Gate Open T_j =150		MIN.	800	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=150		MIN.	3	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j2				

ORDERING INFORMATION 1

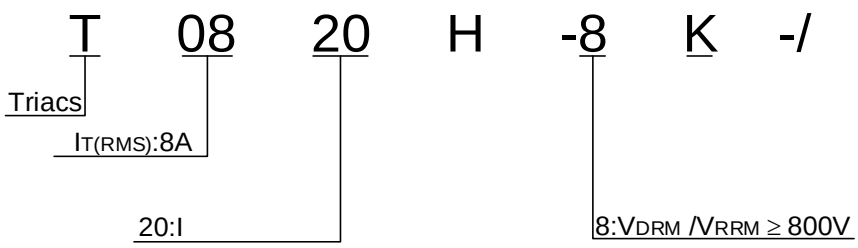


FIG.1: Maximum power dissipation versus RMS on-state current

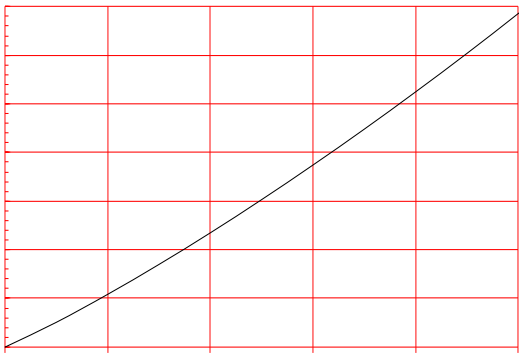


FIG.2: RMS on-state current versus case temperature



FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

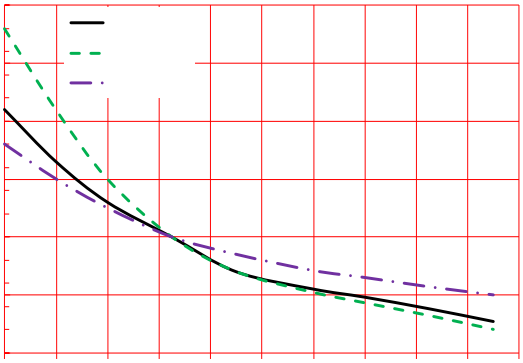
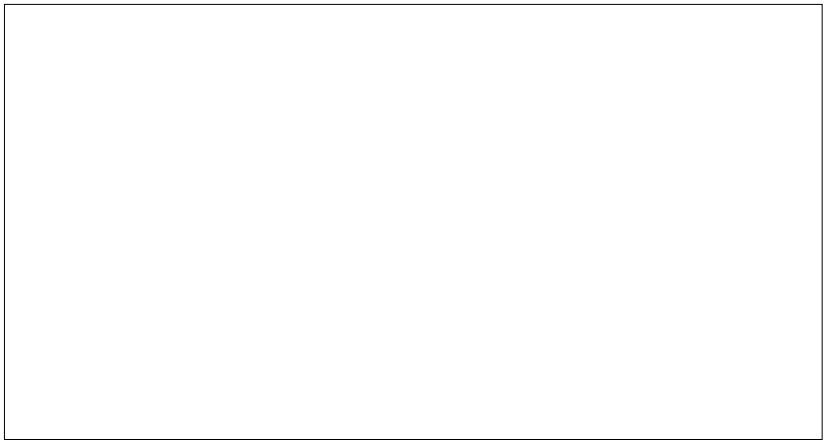
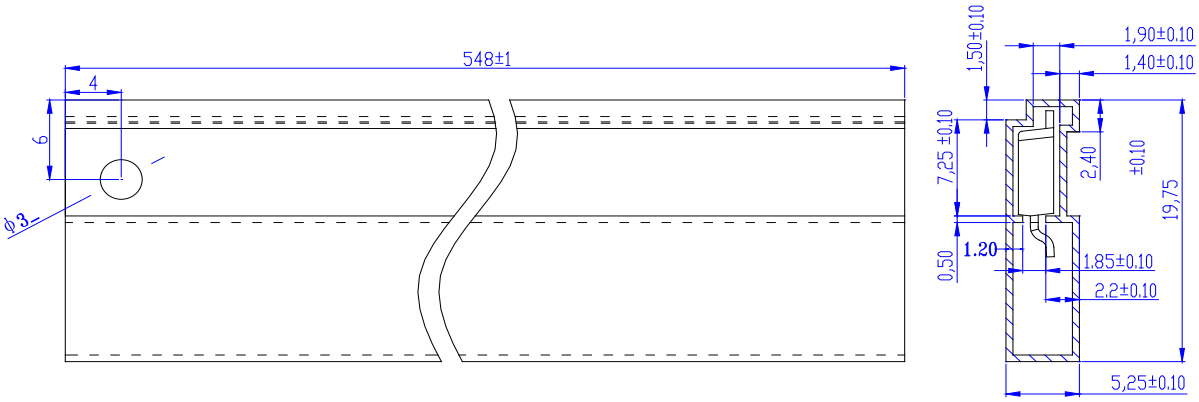


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



DELIVERY MODE



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